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Thyristor High Voltage, Phase Control SCR, 30 A



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PRIMARY CHARACTERISTICS					
I _{T(AV)} 20 A					
V _{DRM} /V _{RRM}	1200 V				
V _{TM}	1.3 V				
I _{GT}	45 mA				
TJ	-40 °C to 125 °C				
Package	TO-247AD 3L				
Circuit configuration	Single SCR				

FEATURES

- AEC-Q101 gualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification



- COMPLIANT HALOGEN FREE
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-30TPS12LHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	20	٨			
I _{RMS}		30	A			
V _{RRM} /V _{DRM}		1200	V			
I _{TSM}		300	A			
V _T	20 A, T _J = 25 °C	1.3	V			
dv/dt		500	V/µs			
di/dt		150	A/µs			
TJ		-40 to +125	°C			

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} / V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} / I _{DRM} AT 125 °C mA			
VS-30TPS12LHM3	1200	1300	10			

VS-30TPS12LHM3



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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS		
Maximum average on-state current	I _{T(AV)}	T _C = 95 °C, 180° conduction	half sine wave	20			
Maximum RMS on-state current	I _{RMS}		30	А			
Maximum peak, one-cycle		10 ms sine pulse, rated V_{RRM} applied		250	A		
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied		300			
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V_{RRN}	A applied	310	A ² s		
Maximum - t for fusing	1-1	10 ms sine pulse, no voltage	442	A-2			
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no volta	4420	A²√s			
Maximum on-state voltage drop	V _{TM}	20 A, T _J = 25 °C	1.3	V			
On-state slope resistance	r _t	T _J = 125 °C		12	mΩ		
Threshold voltage	V _{T(TO)}	IJ= 125 C		1.0	V		
Maximum reverse and direct leakage	1 /1	T _J = 25 °C	V _B = rated V _{BBM} / V _{DBM}	0.5			
current	I _{RM} /I _{DM}	T _J = 125 °C	$v_{\rm R}$ = rated $v_{\rm RRM}$ / $v_{\rm DRM}$	10	mA		
Maximum holding current	Ι _Η	Anode supply = 6 V, resistive	150	ma			
Maximum latching current	١L	Anode supply = 6 V, resistive	200				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 8	$T_J = T_J$ maximum, linear to 80 % V_{DRM} , R_g -k = open				
Maximum rate of rise of turned-on current	dl/dt			150	A/µs		

TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P _{GM}		8.0	w			
Maximum average gate power	P _{G(AV)}		2.0	vv			
Maximum peak positive gate current	+I _{GM}		1.5	А			
Maximum peak negative gate voltage	-V _{GM}		10	V			
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -10 \ ^{\circ}C$	60				
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45 mA				
		Anode supply = 6 V, resistive load, T_J = 125 °C	20				
		Anode supply = 6 V, resistive load, $T_J = -10 \ ^{\circ}C$	2.5				
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0	v			
		Anode supply = 6 V, resistive load, $T_J = 125 \ ^{\circ}C$	1.0	v			
Maximum DC gate voltage not to trigger V _{Gi}		$T_{\rm e} = 125$ °C V $_{\rm even} = rated value$	0.25				
Maximum DC gate current not to trigger	I _{GD}	$T_J = 125 \text{ °C}, V_{DRM} = \text{rated value}$	2.0	mA			

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9				
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	4	μs			
Typical turn-off time	t _q	ij= 125 O	110				

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VS-30TPS12LHM3



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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage T		T _J , T _{Stg}		-40 to 125	°C		
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	0.8	°C/W		
Maximum thermal resistance, junction to ambient		R _{thJA}	DC operation	40			
Maximum thermal resista case to heatsink	ance,	R _{thCS}	Mounting surface, smooth and greased	0.2			
Approvimate weight				6	g		
Approximate weight				0.21	oz.		
Mounting torque	minimum			6 (5)	kgf ⋅ cm		
Mounting torque	maximum			12 (10)	(lĎf ⋅ in)		
Marking device			Case style TO-247AD 3L	30TPS	S12LH		

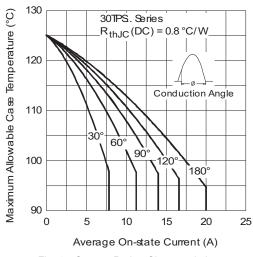
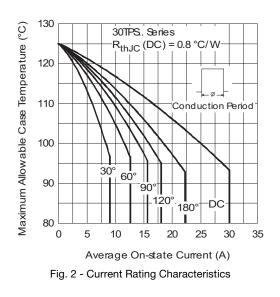


Fig. 1 - Current Rating Characteristics



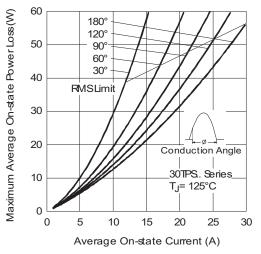
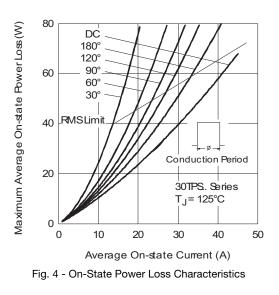


Fig. 3 - On-State Power Loss Characteristics



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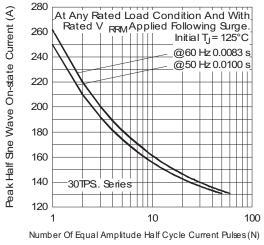
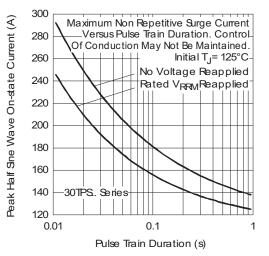
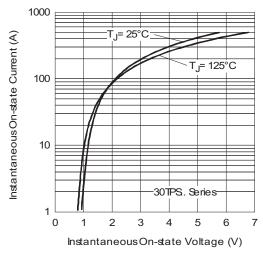
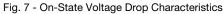


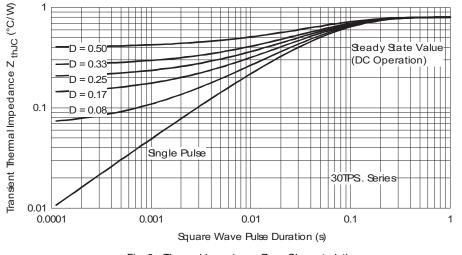
Fig. 5 - Maximum Non-Repetitive Surge Current

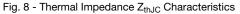












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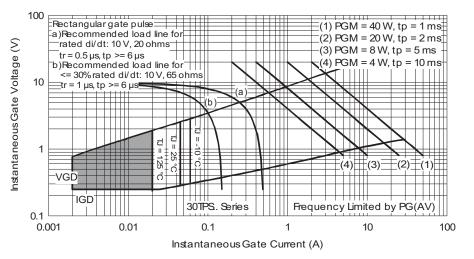


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

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SHA

Device code	VS-	30	т	Р	S	12	L	н	М3
	1	2	3	4	5	6	7	8	9
[1 -	Visł	nay Sem	niconduc	tors pro	duct			
Ī	2 -	Cur	rent rati	ng (30 =	30 A)				
[3 -	Circ	uit conf	iguratior	n:				
		T =	Thyristo	or					
[4 -	P =	TO-247	packag	е				
[5 -	Тур	e of silic	con:					
		S =	Standa	rd recov	ery recti	fier			
l	6 -	Volt	age cod	le x 100	= V _{RRM}		12	= 1200	V
[7 -	Pac	kage L	= long le	ad				
[8 -	H =	AEC-Q	101 qua	lified				
[9 -	Envi	ronmen	tal digit:					
		M3 =	= haloge	en-free, l	RoHS-c	omplian	t, and te	erminati	ions lea

ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-30TPS12LHM3	25	500	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS					
Dimensions TO-247AD 3L www.vishay.com/doc?95626					
Part marking information	TO-247AD 3L	www.vishay.com/doc?95007			

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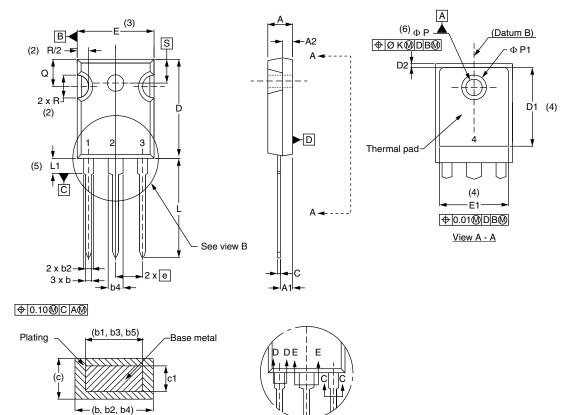
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TO-247AD 3L

DIMENSIONS in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

(2, 52, 51) (4) Section C - C, D - D, E - E

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØК	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

- ⁽³⁾ Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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